

Monitoring the structural transformation on thin films of an Asymmetric Benzothieno[3,2-b][1]-benzothiophene Derivative

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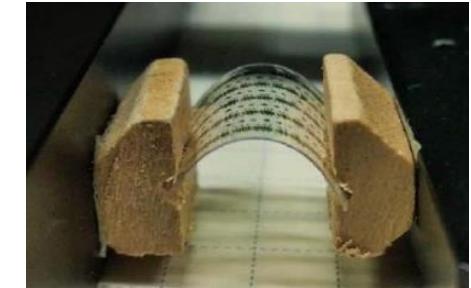
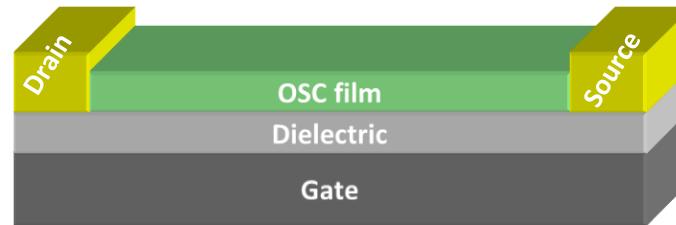
² ALBA Synchrotron



Organic Semiconductor (OSCs) Devices

- ❖ Low-temperature processing
- ❖ Low-cost production
- ❖ Mechanical flexibility
- ❖ Light weight
- ❖ Large range of tunability

Organic-field-effect transistors
OFETs



Debdatta Panigrahi *et al* 2021 *Appl. Phys. Express* **14** 081004

Mobility critically determined by the **crystal structure and crystalline order**, particularly at the interface



Thermal treatment of the as-grown films is a common strategy to improve the crystalline order

Key factors in thermal behaviour

Temperature might induce:

Polymorphism

- A common phenomenon due to the **non-covalent interactions** in organic crystals.
- A large impact for the charge transport and stability of the devices: Need of characterization and control

Inhomogeneous strain

Coefficient of Thermal Expansion (CTE)

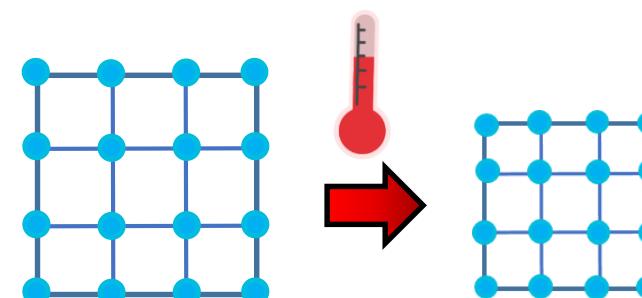
$$CTE = \frac{1}{d} \left(\frac{\Delta d}{\Delta T} \right)$$

SiO₂/Al₂O₃ : $4 - 5 \times 10^{-6} K^{-1}$

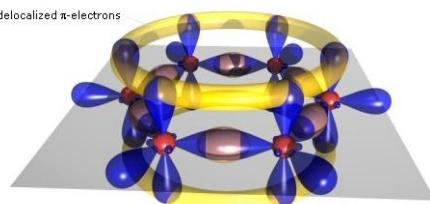
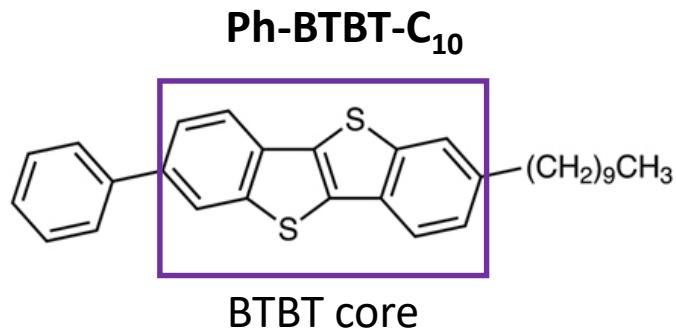
OSC : $100 - 300 \times 10^{-6} K^{-1}$

- Large CTE Mismatch at the Semiconductor–Dielectric Interface
- Anisotropy and Negative thermal expansion

Thermal expansion and strain have been poorly investigated in correlation with polymorphism



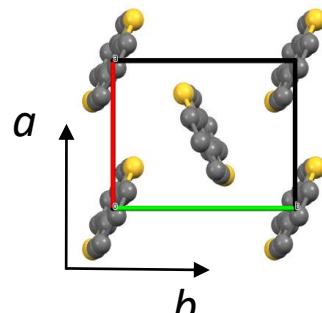
Small molecule organic semiconductors: BTBT derivatives



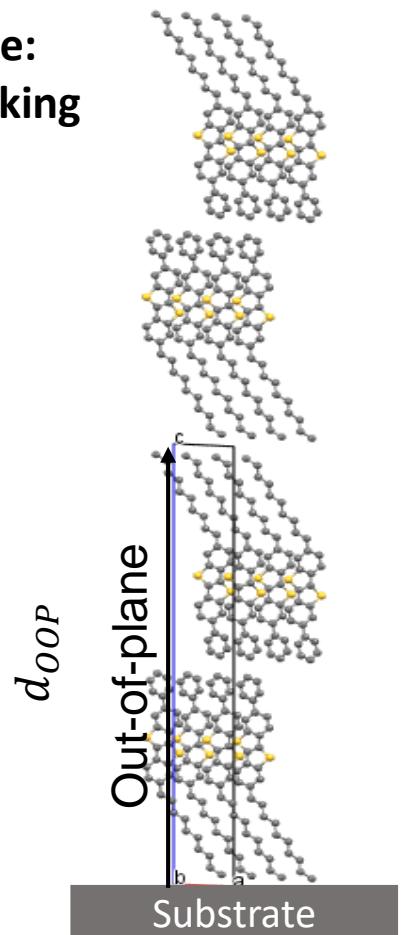
- ✓ Mobility comparable to polysilicon devices ($1 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$)
- ✓ Highly ordered crystalline layers (lamellar structures)
- ✓ Air-stable devices

[1]benzothieno[3,2-b][1]-benzothiophene

The single-crystalline structure:
monoclinic with a bilayer-packing



Herringbone arrangement of
BTBT core



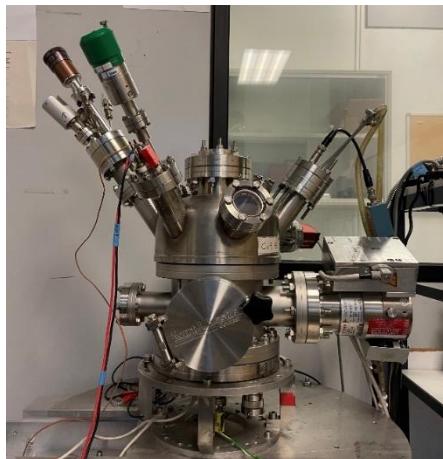
However, Ph-BTBT-C10 thin films exhibit polymorphism

Goals & Experiments

Goals :

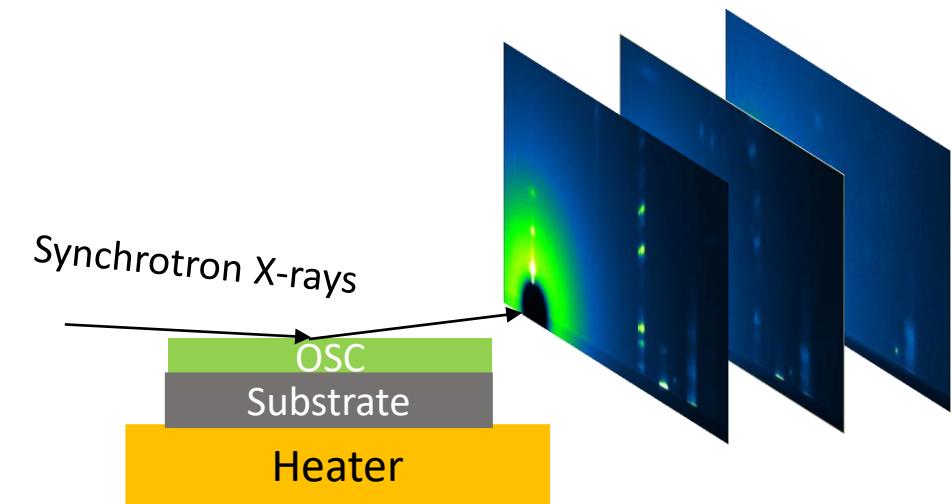
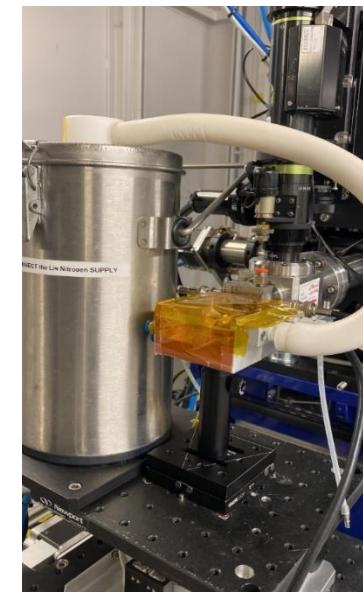
- Structural transformations with temperature
- Thermal expansion and strain for the different Ph-BTBT-C10 polymorphs

Film prepared by
vacuum sublimation



The substrate is native SiO_2
Film thickness: 20 nm and 40 nm

Grazing-Incidence Wide Angle X-ray Scattering
(GIWAXS)

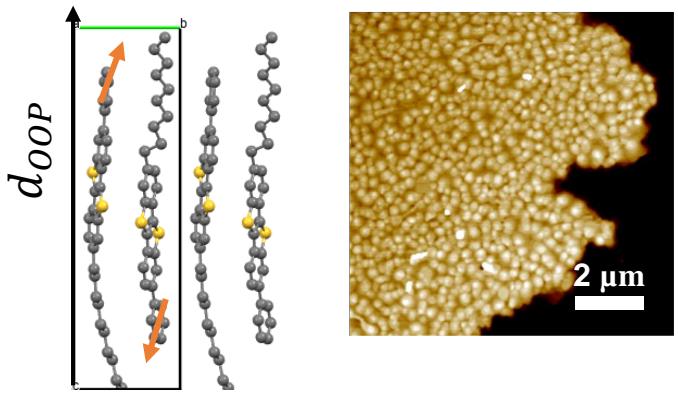


GIWAXS experiments were performed at
NCD-SWEET Beamline at ALBA Synchrotron

Polymorphism of Ph-BTBT-C10 thin-films

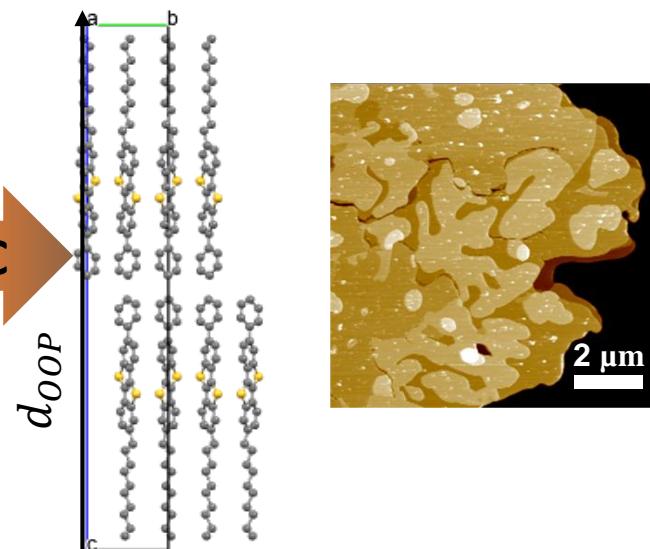
Same herringbone arrangement of BTBT cores in the in-plane

Single-layer
metastable phase



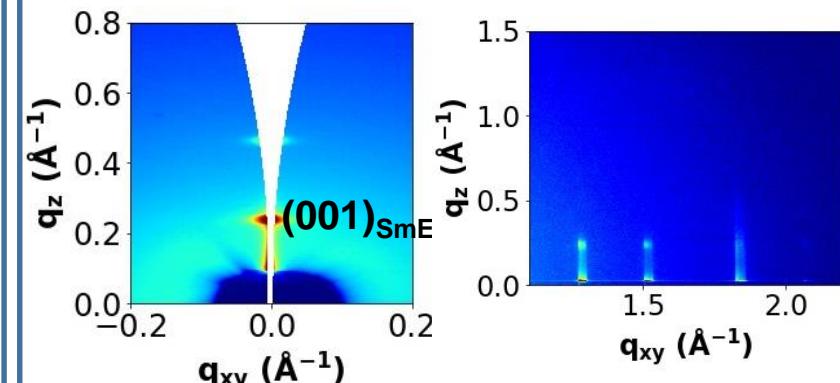
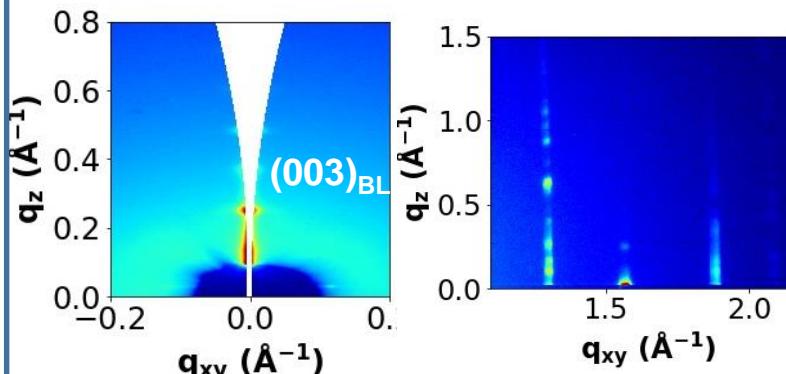
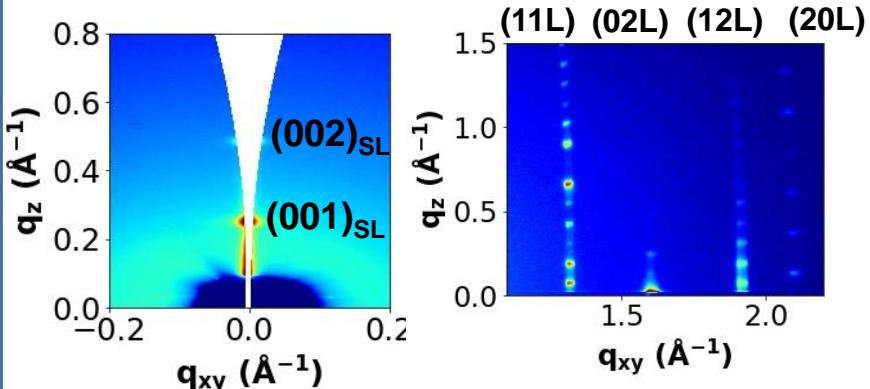
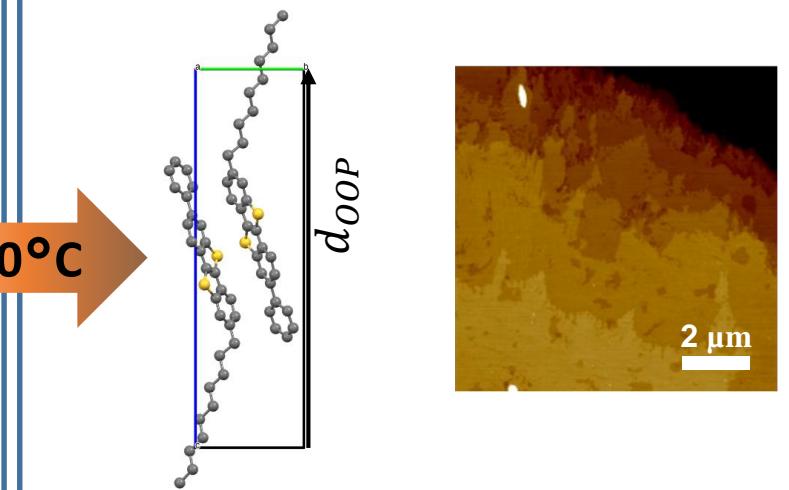
120°C

Bilayer
Head to head

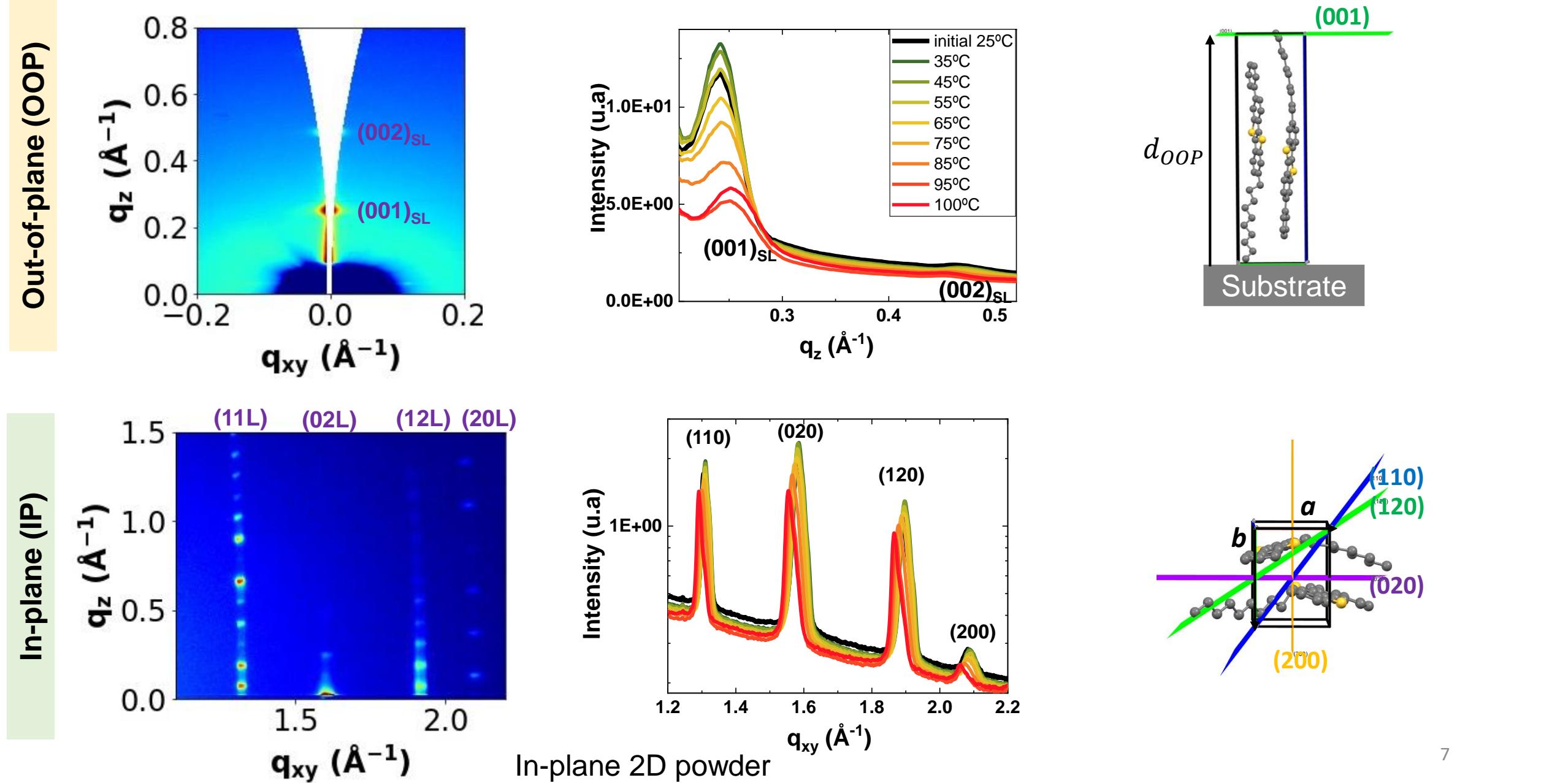


150°C

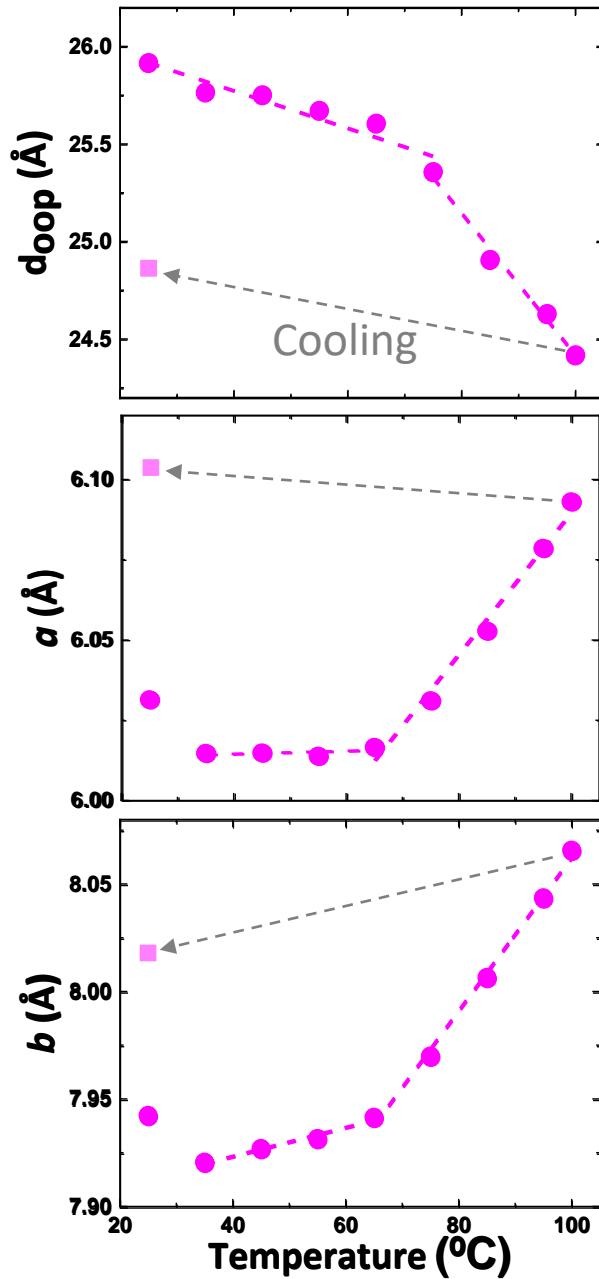
Single-layer
Liquid Crystal - Smetic E



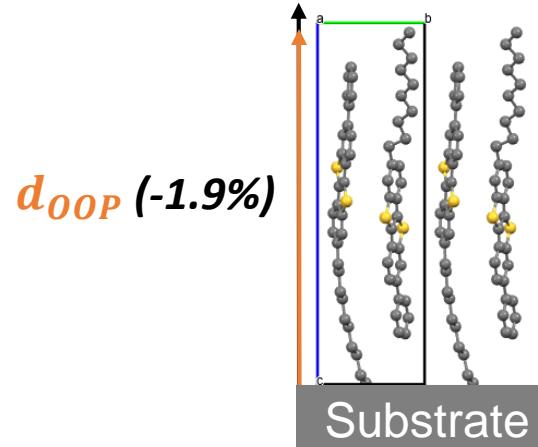
Single-Layer structure



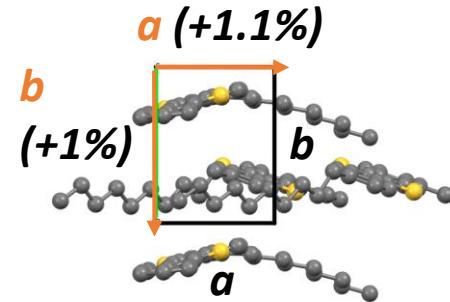
Strain on Single-Layer structure



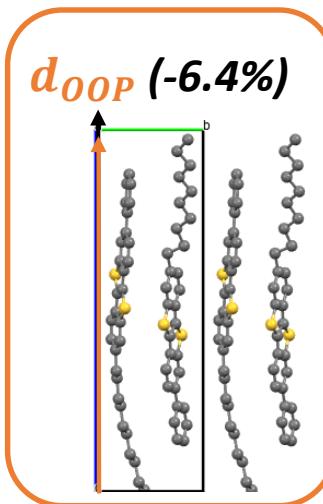
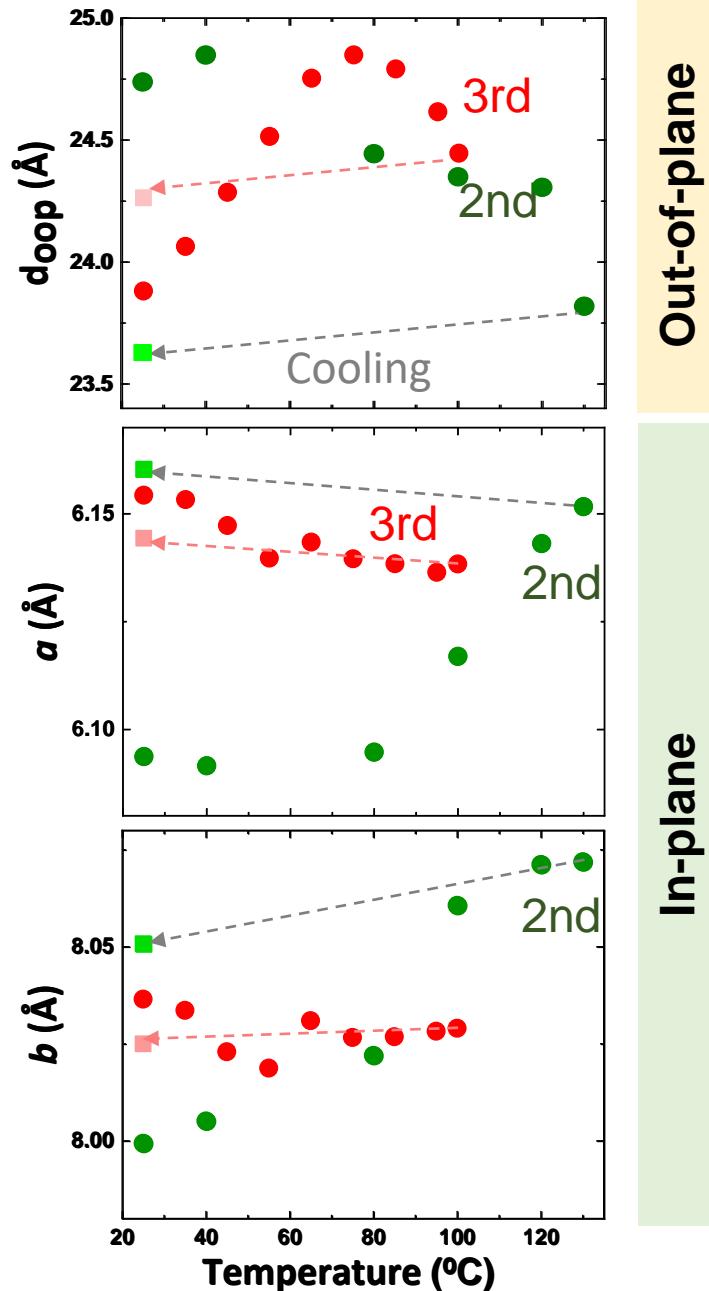
With thermal annealing



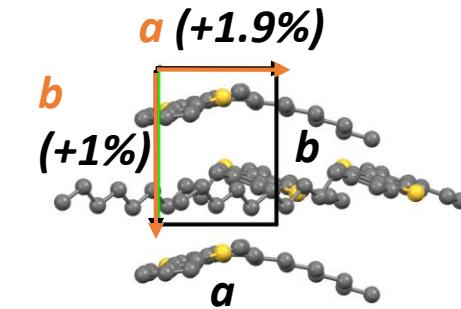
- Anisotropic and non-linear expansion with temperature.
- Irreversible changes: Reduction of the out-of-plane direction and expansion of in-plane unit cell.



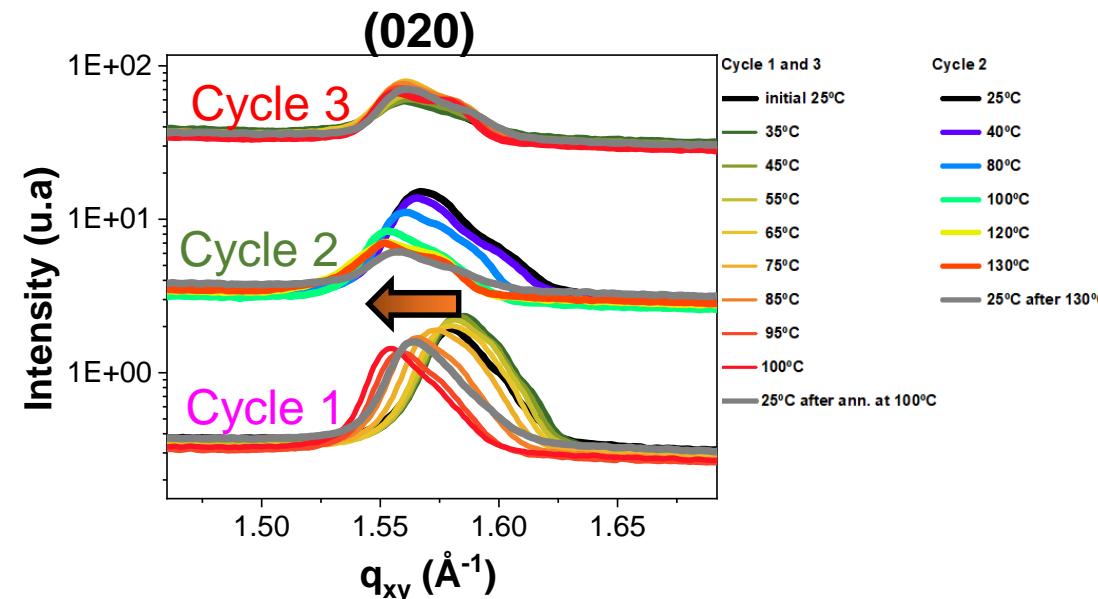
Thermal Cycling



After 3 annealing cycles

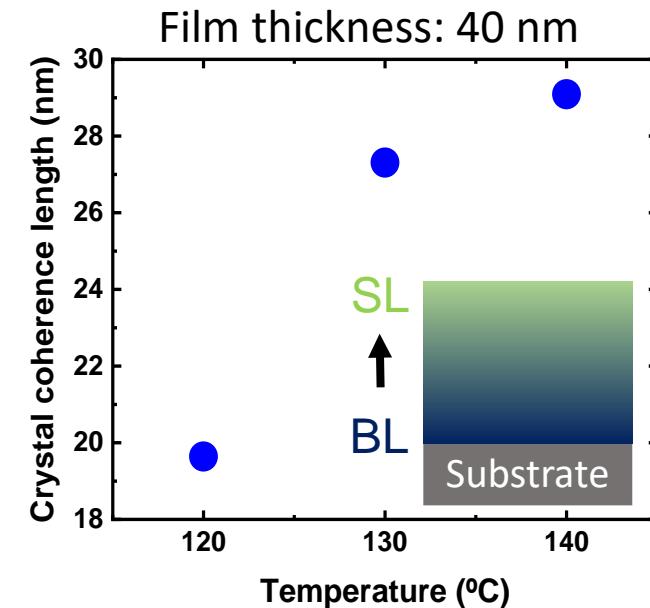
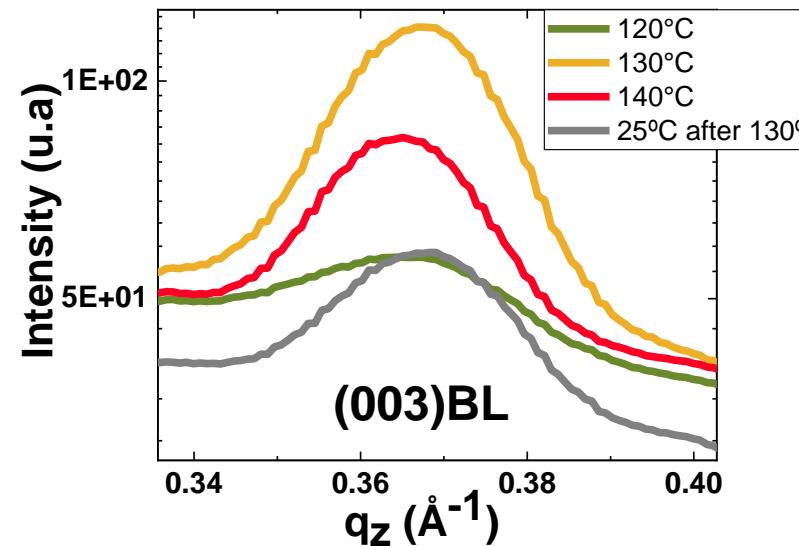
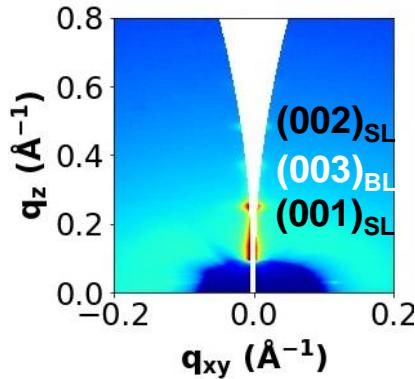


□ The in-plane strain is released after 2 annealing cycles

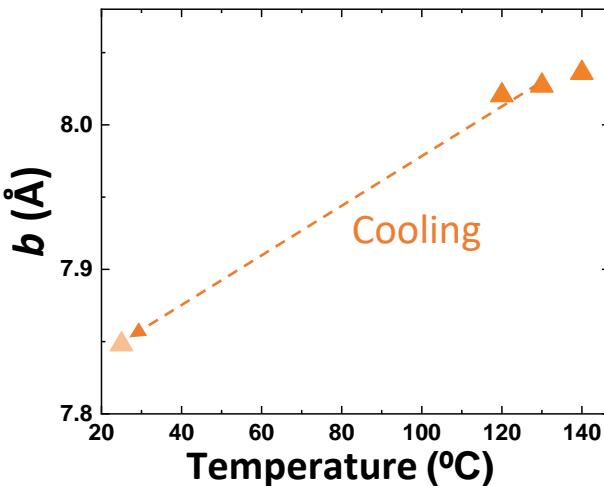


Bilayer structure

Out-of-plane



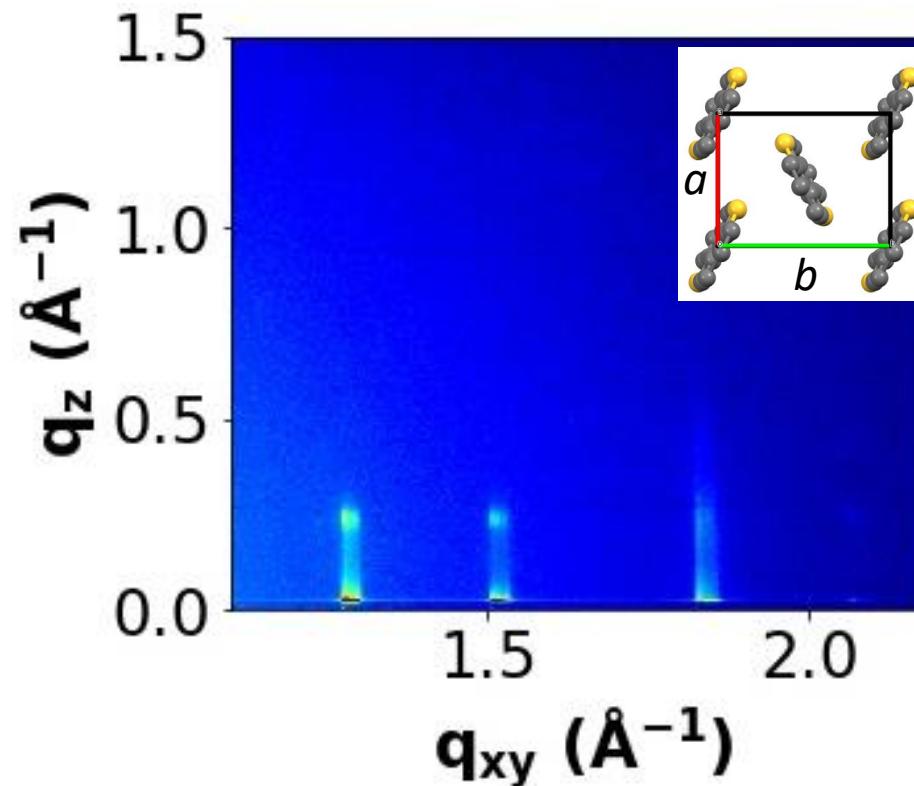
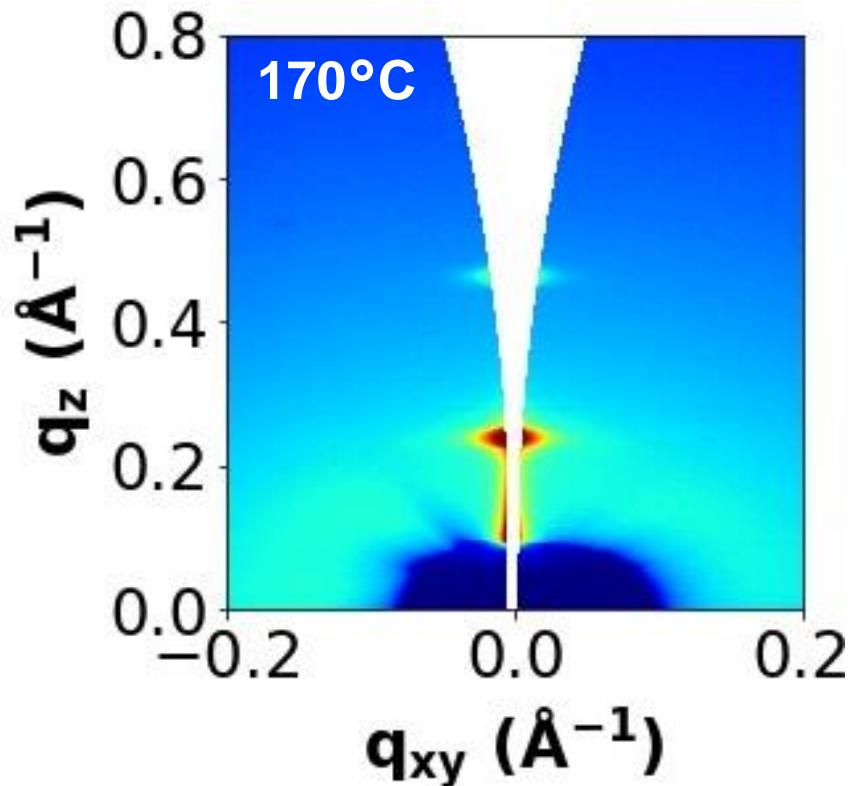
In-plane



- Bilayer emerges above 120 °C and develops with further annealing: SL-BL transformation occurs in the vertical direction
- No thermal expansion along the out-of-plane direction (stronger interlayer interaction for the bilayer packing)
- Expansion between room temperature and 140 °C along b -axis ($CTE_b = 17 \times 10^{-6} \text{ K}^{-1}$)

SmE Single-Layer structure

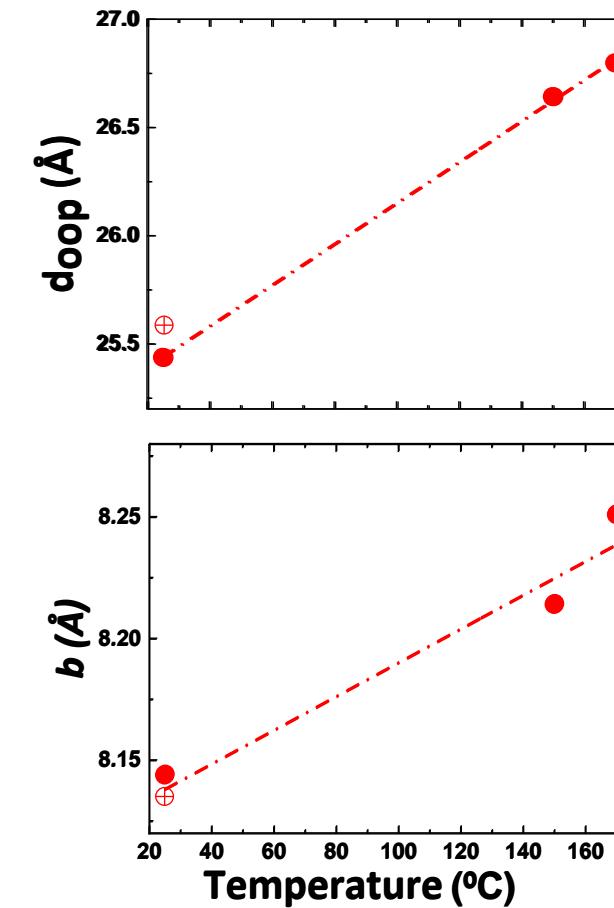
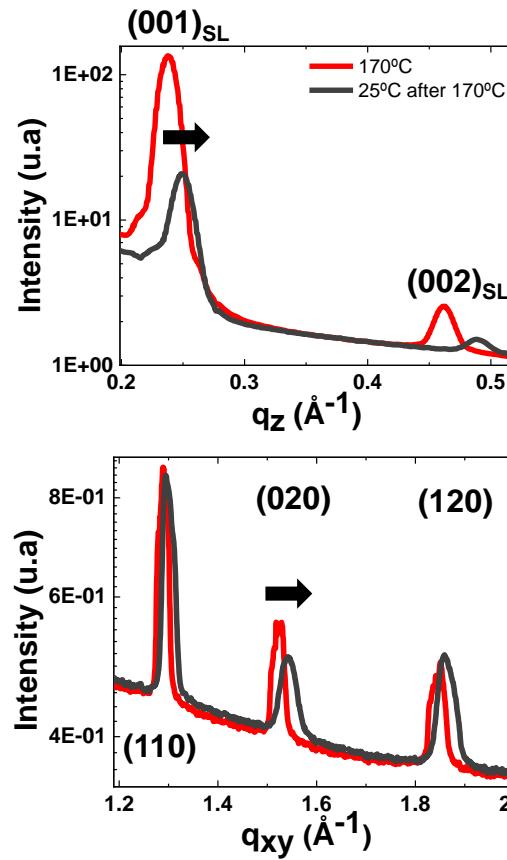
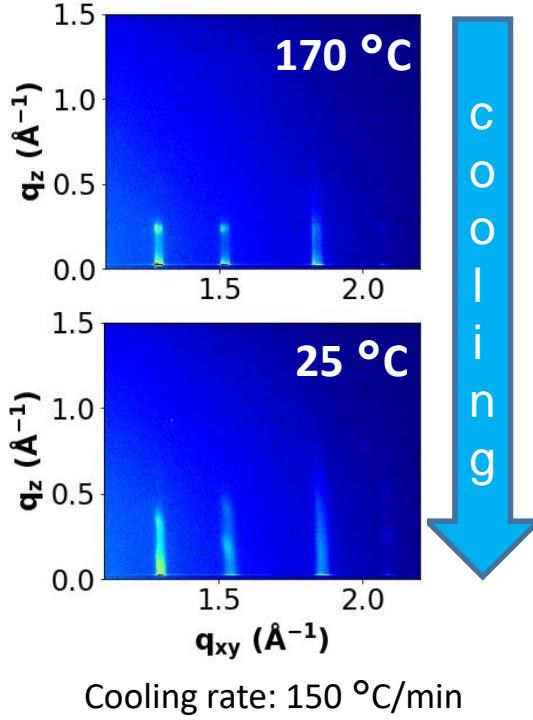
It forms for $T > 150^{\circ}\text{C}$



- In-plane: Herringbone BTBT packing
- OOP: Short-range order
- Recently proposed: molten alkyl chains

[Saito et al., Journal of Chemical physics, vol.139, p.114902, 2013]

Thermal expansion on Smetic E structure



Out-of-plane

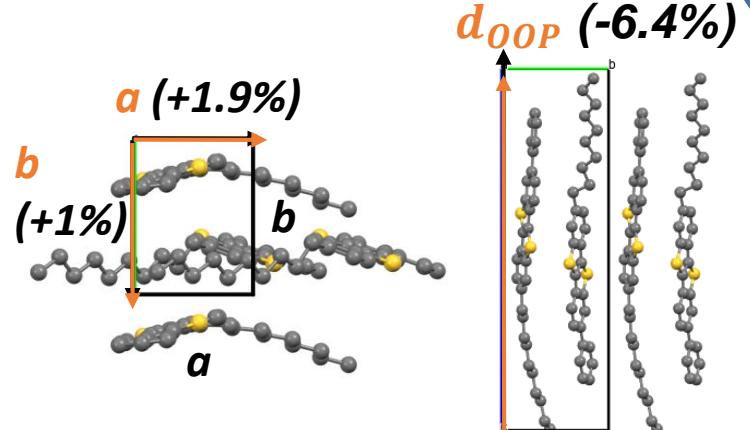
In-plane

- Liquid crystalline phase smE remains at room temperature (after cooling down)
- Anisotropic ‘colossal’ thermal expansion on smetic E phase.** Largest expansion along the out-of-plane direction

Parameter	CTE ($10^{-6} K^{-1}$)
d_{OOP}	350
b	89

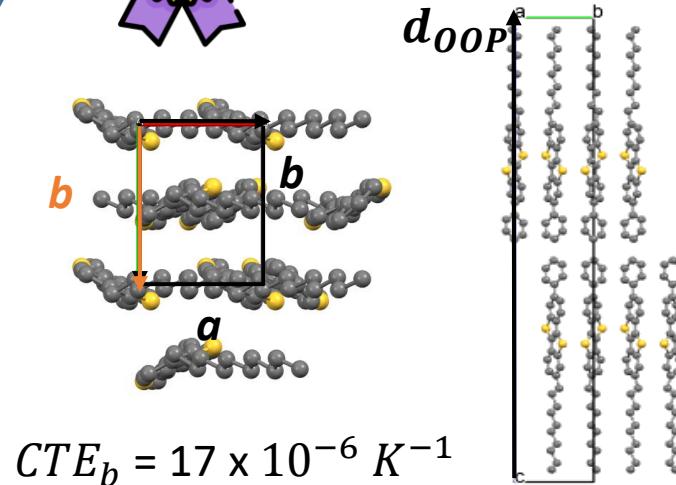
Summary

Single Layer



- STRAIN: Anisotropic and non linear changes with temperature.
- In-plane structure stabilized after 3 annealing cycles

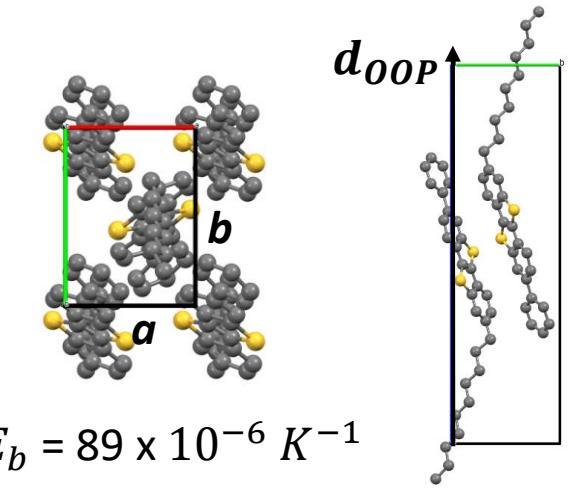
Bilayer



$$CTE_b = 17 \times 10^{-6} K^{-1}$$

- Stable phase
- Anisotropic **thermal expansion**: only along *b*-axis.

SmecticE



$$CTE_b = 89 \times 10^{-6} K^{-1}$$

$$CTE_{d_{oop}} = 350 \times 10^{-6} K^{-1}$$

- Anisotropic and ‘colossal’ **thermal expansion**, largest along out-of-plane direction.

Implication in OFETs

Lack of reproducibility

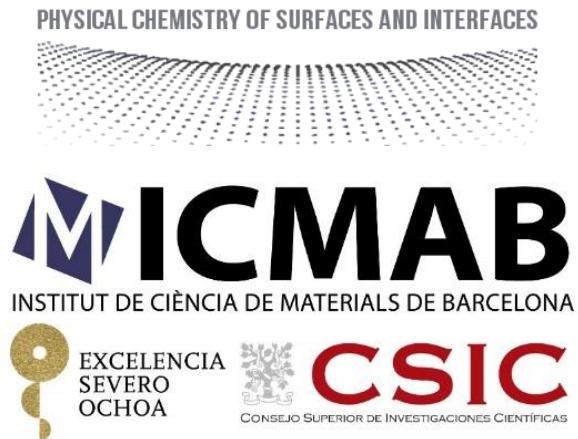
Tightest packing, highest mobility

Cracks on the film

Acknowledgement

PCSI Group members:

Prof. Carmen Ocal
Dr. Esther Barrena
Dr. Daniel Martín
Dr. Rogger Palacios
Shunya Yan
Georgios Atsas
Rodrigo Arilla



ALBA Staff (NCD-SWEET Beamline):

Dr. Eduardo Solano



GIWAXS experiments were performed at the beamline BL11-NCD-SWEET at ALBA Synchrotron with the collaboration of ALBA staff.

Funding:

Spanish Ministry of Science and Innovation (MCIN) and State Investigation Agency (AEI) under project PID2022-136802NB-I00 (AEI/FEDER, UE) and through the Severo Ochoa Programme for Centres of Excellence in R&D (CEX2023-001263-S).



In situ Correlative Facility for Advanced Energy Materials (InCAEM) project

Finançat per:



Crystal structure of asymmetric organic semiconductor
7-decyl-2-phenyl[1]benzothieno[3,2-*b*][1]benzothiophene

Single crystal of Ph-BTBT-C10 present the BL packing

Hiromi Minemawari^{1*}, Jun'ya Tsutsumi¹, Satoru Inoue¹, Toshikazu Yamada¹,
Reiji Kumai², and Tatsuo Hasegawa^{1,3}

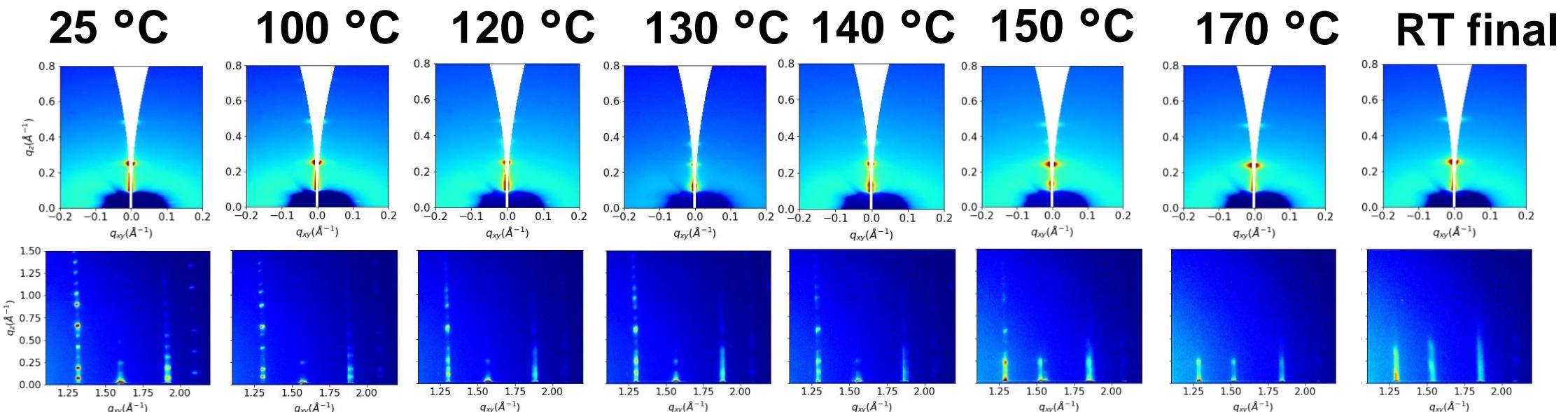
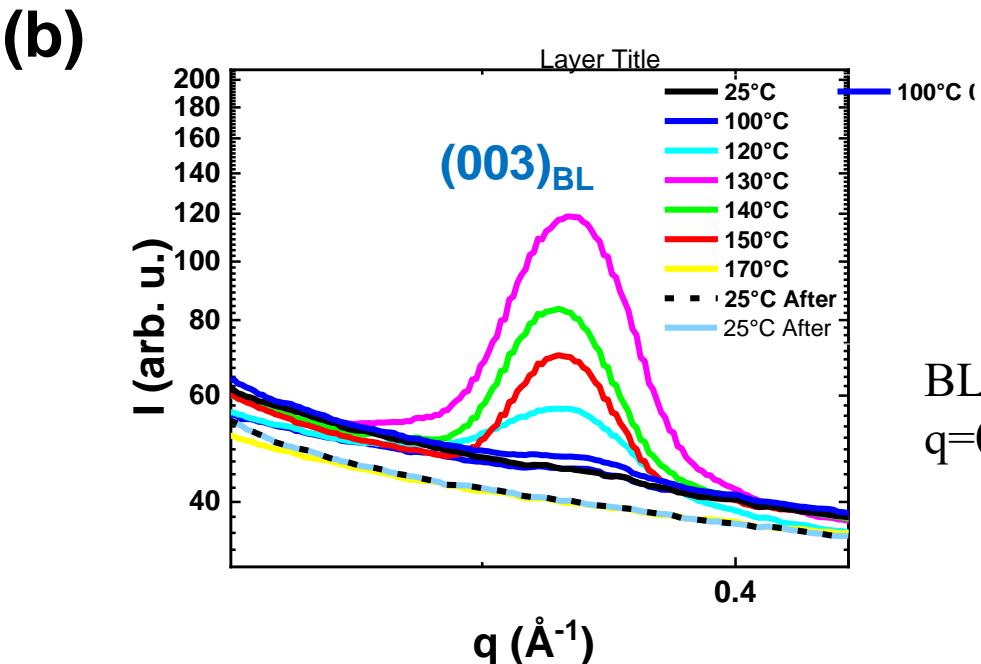
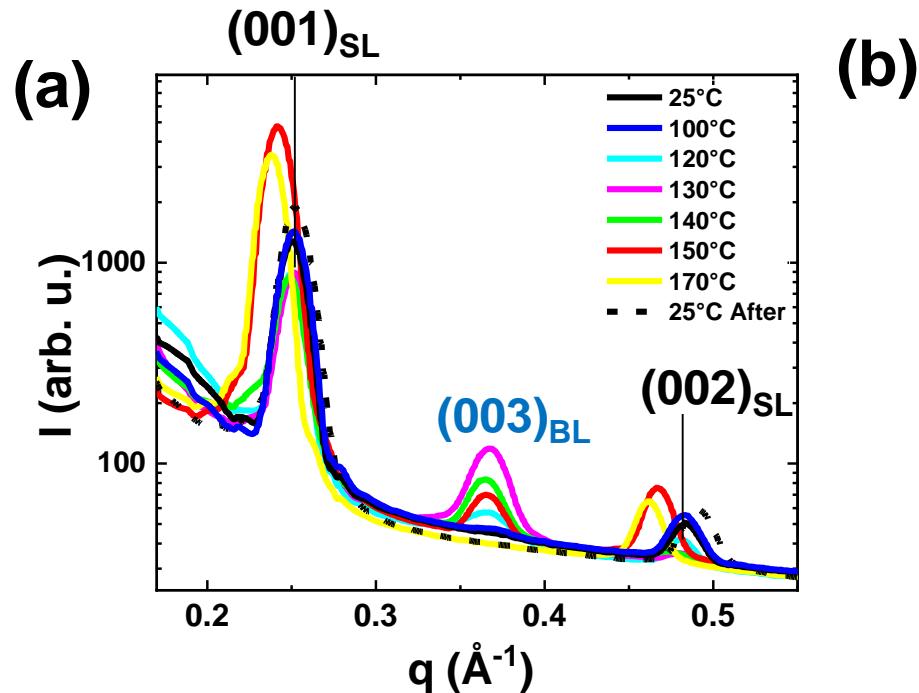
For a sample of 40 nm (L1) the unit cell parameters of the different polymorphs at room temperature are:

	a	b	doop monolayer
SL	5.97	7.82	25.4
BL	6.03	7.85	25.6
smE	6.02	8.15	25.2
Single crystal (BL)	6.04	7.76	26.56

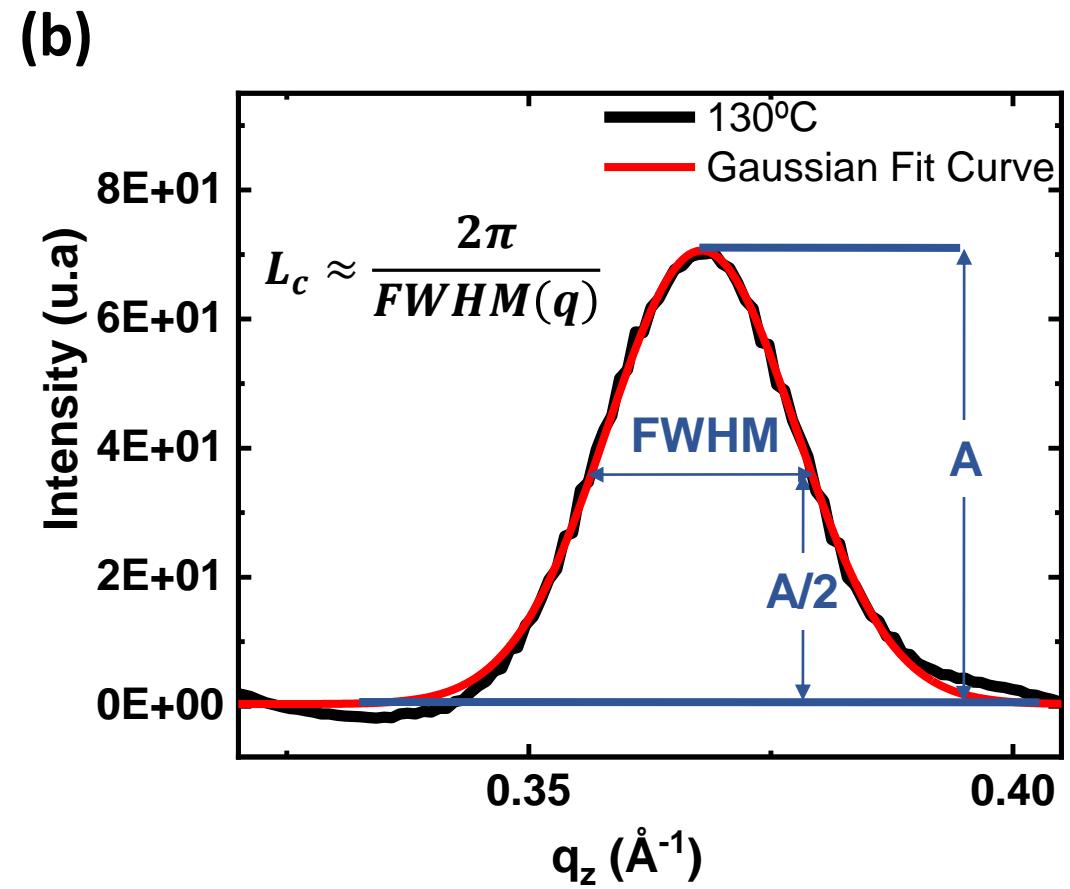
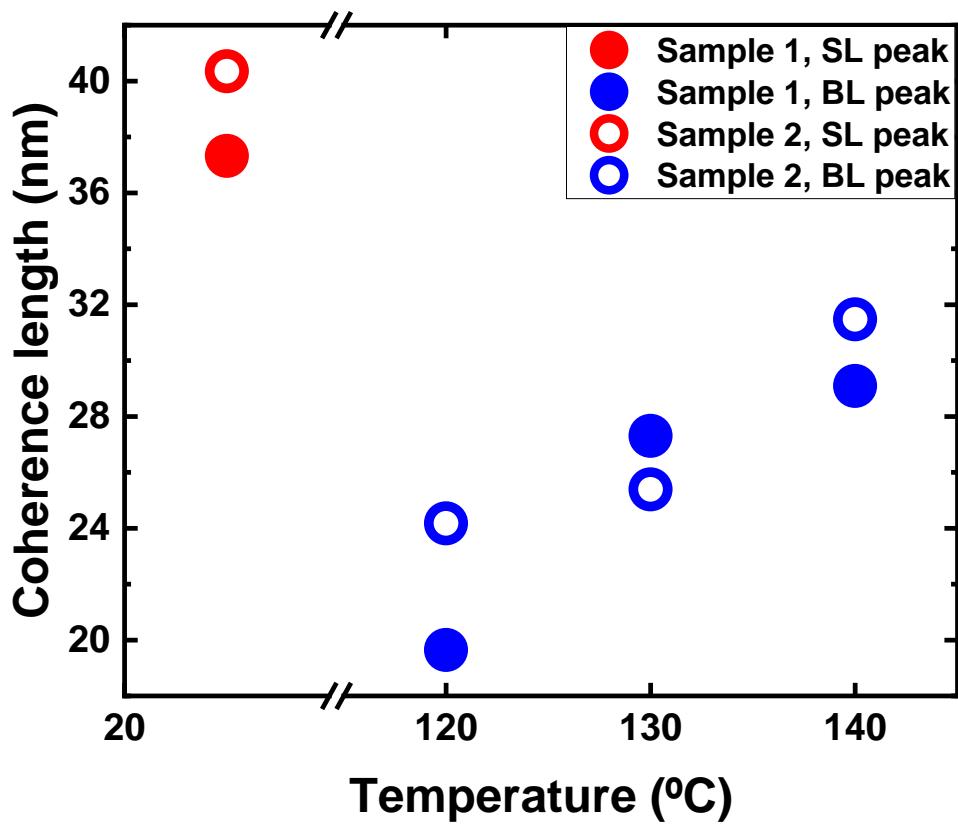
For SL is the value at initial RT

For BL is the value at RT after annealing at 130°C

For smE is the value at RT after annealing at 170°C



2D GIWAXS images for all the measured temperatures



Crystal coherence length calculated from the FWHM values of the (001) SL peak at initial 25 °C and of (003) BL peak at certain temperatures.

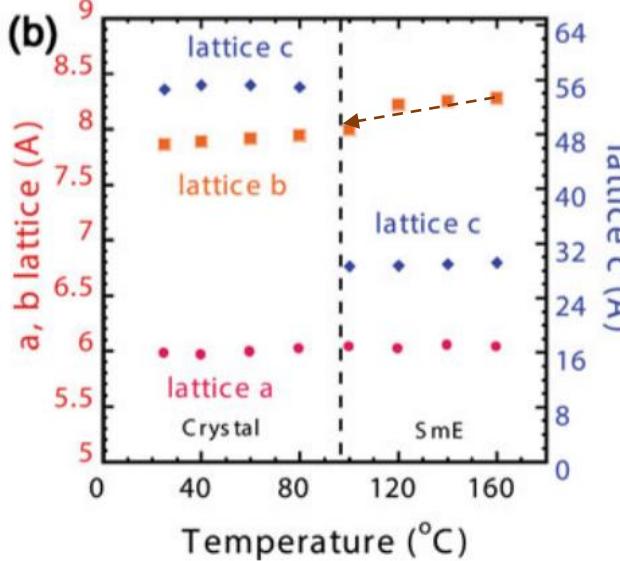
smE as a precursors for crystalline films

Liquid crystal and crystal structures of a phenyl-benzothienobenzothiophene derivative

Hiroaki Iino and Jun-ichi Hanna

They prepare the crystal phase (Bilayer) from the smE pase upon cooling. A thick (10 um) and thin (50 nm) films are prepared on **glass substrates**.

Parameters evolution during the cooling process on the 10 um bulk film:

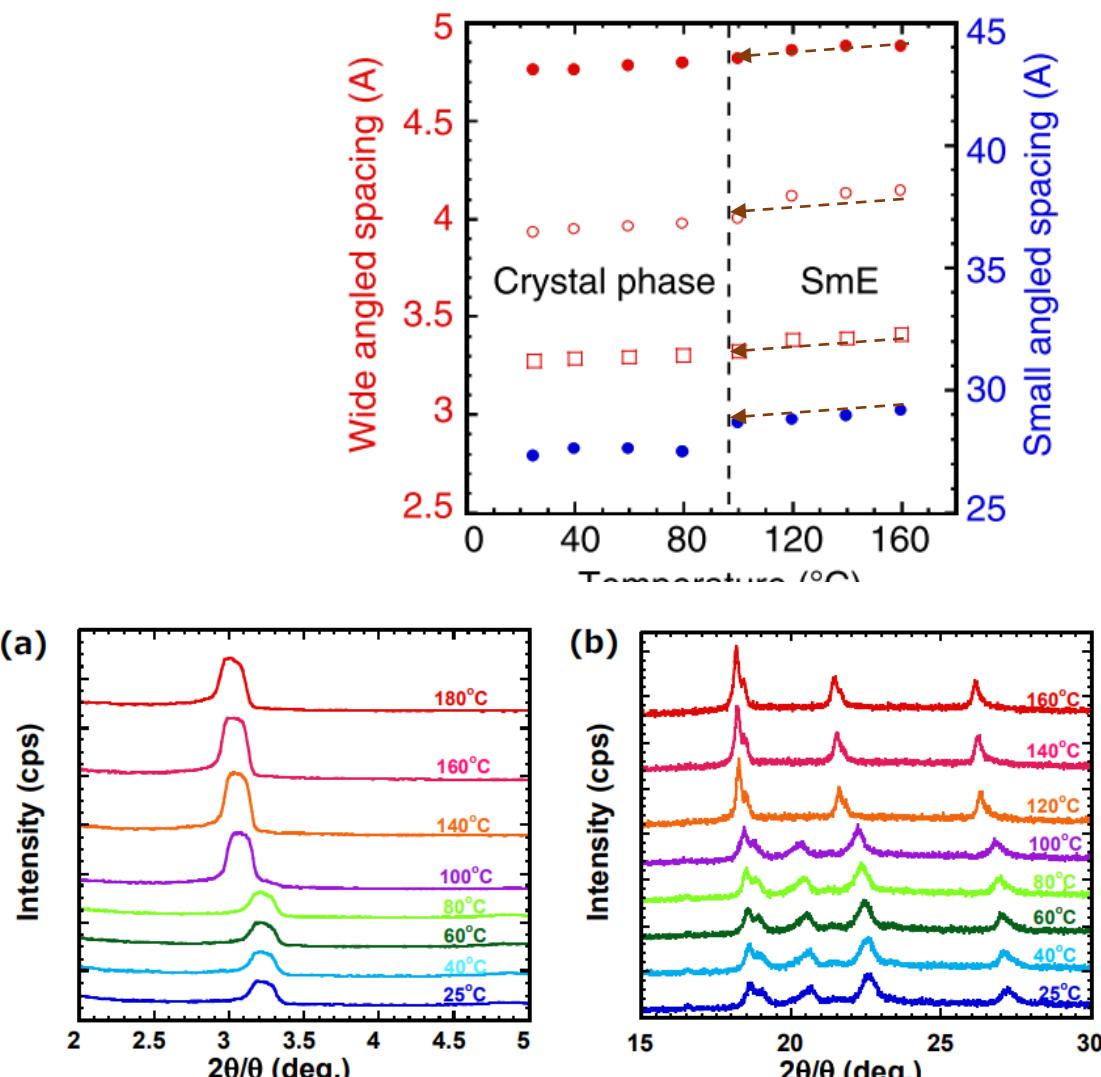


Comparison BL-smE:
Shorter b in BL
Doubled c in BL
Same a

Evolution of smE parameters with temperature:
Decrease of b with cooling temperatures
No change on a or c in the temperaturas o smE

Liquid crystals for organic thin-film transistors

Hiroaki Iino^{1,2}, Takayuki Usui^{1,2} & Jun-ichi Hanna^{1,2}

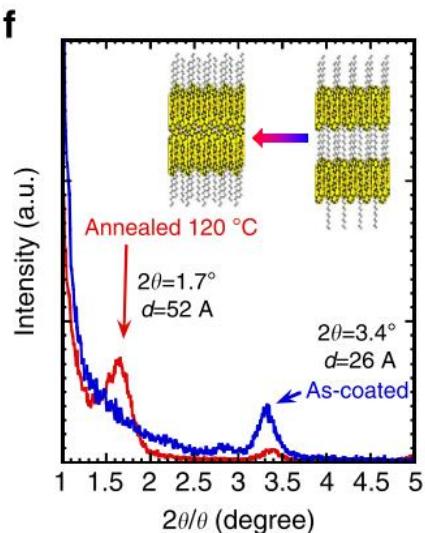
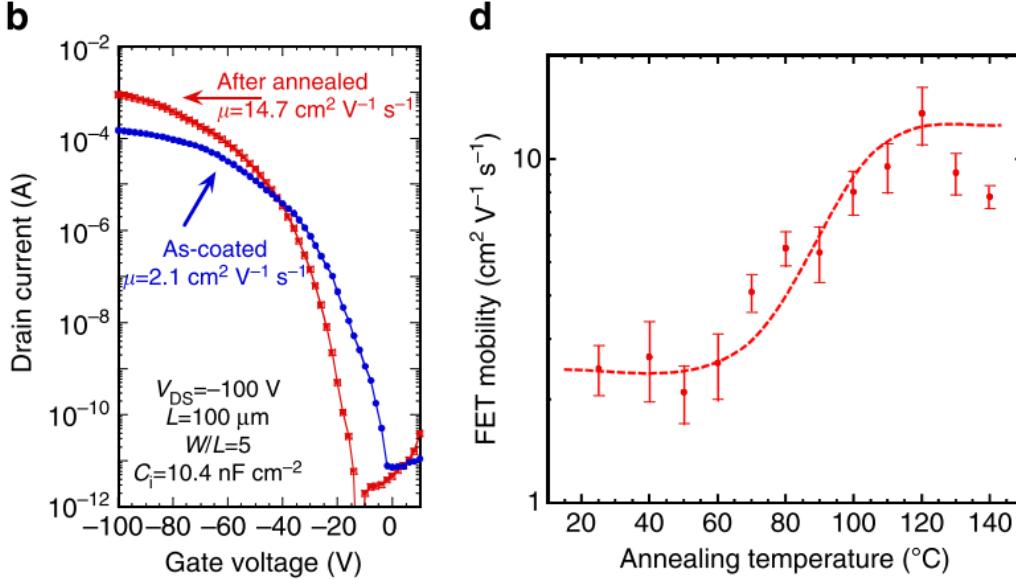


Supplementary Figure 2 | XRD patterns of Pb-BTBT 10 at several temperatures.

Liquid crystals for organic thin-film transistors

Hiroaki Iino^{1,2}, Takayuki Usui^{1,2} & Jun-ichi Hanna^{1,2}

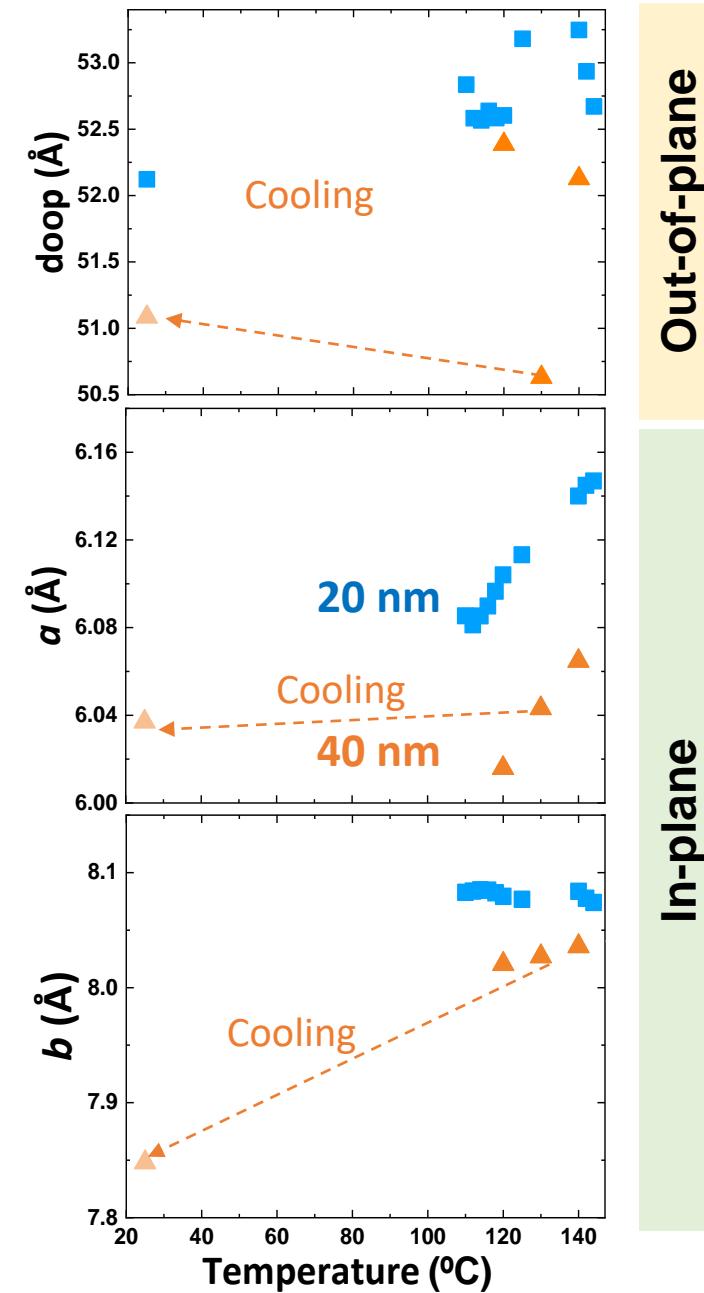
Top contact – bottom gate OFETs



FET mobility improved after thermal annealing at 120 °C for 5 min from $2.1 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$ up to $14.7 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$ due to the transition from monolayer to bilayer phase

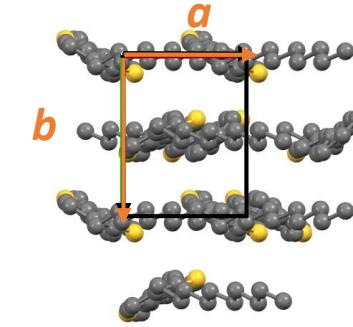
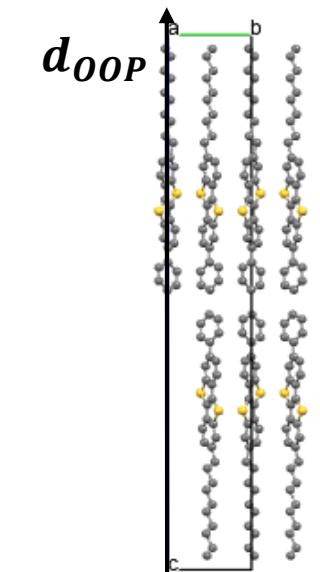
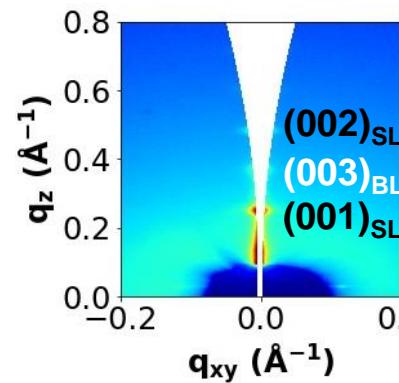
*Prepared from solution

Thermal expansion on Bilayer structure



Out-of-plane

In-plane



- ❑ No thermal expansion along the out-of-plane direction (stronger interlayer interaction for the bilayer packing)
- ❑ Largest expansion between room temperature and 140 $^{\circ}\text{C}$ is along b -axis ($CTE_b = 17 \times 10^{-6} \text{ K}^{-1}$)

Outlook

- Measure in situ the OFETs while annealing. See if the strain have an impact on the charge trapping. See if it is possible to minimize by thermal treatment.
- Strain effects with different substrates (different mismatch between the coefficient of thermal expansion)
- Role of the side groups (alkyl chain length, phenyl groups..) on the strain effects